General Purpose Transistors

PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CEO}	-65 -45 -30	>
Collector-Base Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CBO}	-80 -50 -30	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous	I _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	P _D	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	883	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

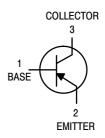
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



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SC-70/SOT-323 CASE 419 STYLE 3

MARKING DIAGRAM



xx = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

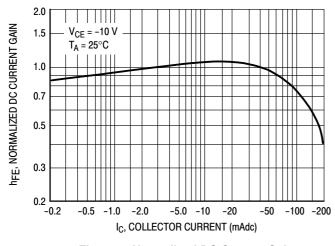
Cha	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		· ·		ı	ı	
Collector – Emitter Breakdown Vo (I _C = -10 mA)	ltage BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _(BR) CEO	-65 -45 -30	- - -	- - -	V
Collector – Emitter Breakdown Vo (I _C = –10 μA, V _{EB} = 0)	ltage BC856, SBC856 Series BC857B, SBC857B Only BC858 Series	V _{(BR)CES}	-80 -50 -30	- - -	- - -	V
Collector – Base Breakdown Volta (I _C = –10 μA)	BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)CBO}	-80 -50 -30	- - -	- - -	V
Emitter – Base Breakdown Voltag ($I_E = -1.0 \mu A$)	e BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)EBO}	-5.0 -5.0 -5.0	- - -	- - -	V
Collector Cutoff Current (V _{CB} = (V _{CB} =	I _{CBO}	_ _	- -	-15 -4.0	nA μA	
ON CHARACTERISTICS			!	!	!	!
DC Current Gain (I _C = -10 µA, V _{CE} = -5.0 V) SBC857B BC858B	BC856A, BC585A BC856B, SBC856B, BC857B,	h _{FE}	_ _	90 150	_ _	_
3BC637B BC636B	BC857C		_	270	_	
$(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ SBC857B, BC858B	BC856A, BC858A BC856B, SBC856B, BC857B,		125 220	180 290	250 475	
,		420	520	800		
Collector – Emitter Saturation Volt (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{CE(sat)}	- -	- -	-0.3 -0.65	V	
Base – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	,	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage $ \begin{pmatrix} I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V} \\ (I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V}) \end{pmatrix} $		V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERIS	STICS					
Current – Gain – Bandwidth Produ (I _C = –10 mA, V _{CE} = –5.0 Vdc,	fT	100	-	-	MHz	
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{ob}		-	4.5	pF	
Noise Figure ($I_C = -0.2$ mA, $V_{CE} = -5.0$ Vdc, $f = 1.0$ kHz, BW = 200 Hz)	, R _S = 2.0 kΩ,	NF	_	-	10	dB

-0.9

T_A = 25°C

-0.1 -0.2

BC857/SBC847/BC858



-0.8
| V_{BE(sat)} @ I_C/I_B = 10
| V_{BE(on)} @ V_{CE} = -10 V
| V_{BE(on)} @ V_{CE} = -10 V
| V_{BE(on)} @ V_{CE} = 10 V

-2.0

-1.0

Figure 1. Normalized DC Current Gain

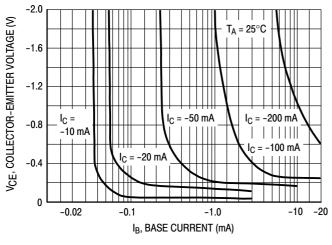
I_C, COLLECTOR CURRENT (mAdc)

Figure 2. "Saturation" and "On" Voltages

-5.0

-50

-100



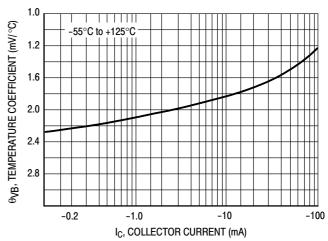
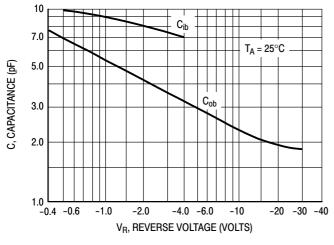


Figure 3. Collector Saturation Region

Figure 4. Base-Emitter Temperature Coefficient



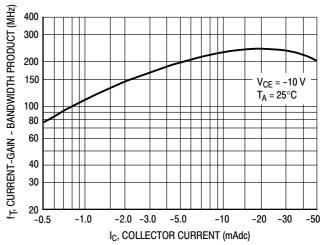


Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product

BC856/SBC856

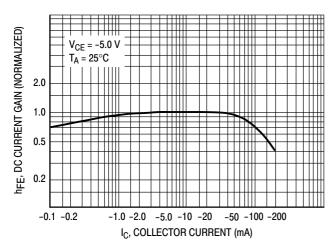


Figure 7. DC Current Gain

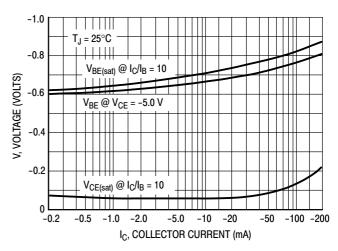


Figure 8. "On" Voltage

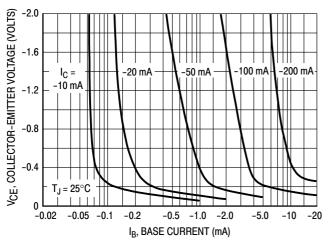


Figure 9. Collector Saturation Region

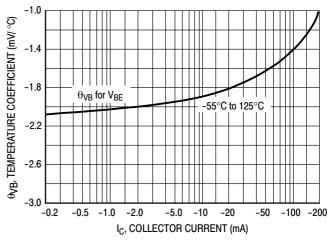


Figure 10. Base-Emitter Temperature Coefficient

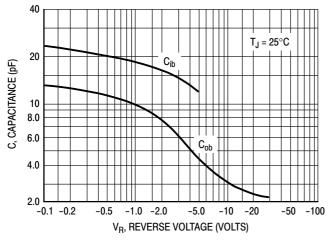


Figure 11. Capacitance

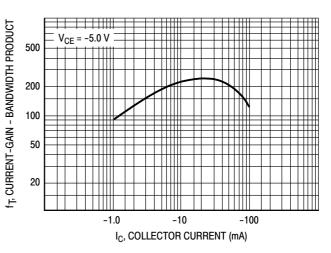


Figure 12. Current-Gain - Bandwidth Product

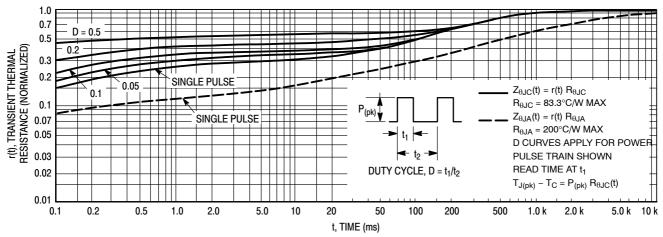


Figure 13. Thermal Response

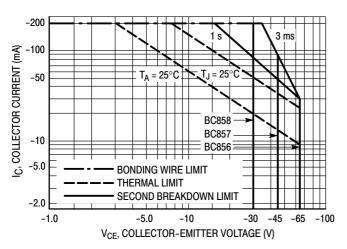


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

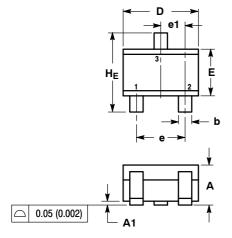
ORDERING INFORMATION

Device	Marking	Package	Shipping [†]	
BC856BWT1G	ap.	SC-70/SOT-323	2 000 / Tono % Dool	
SBC856BWT1G	- 3B	(Pb-Free)	3,000 / Tape & Reel	
BC857BWT1G	3F	SC-70/SOT-323	3,000 / Tape & Reel	
SBC857BWT1G	- SF	(Pb-Free)	3,000 / Tape & Reel	
BC857CWT1G	3G	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	
BC858AWT1G	3J	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	
BC858BWT1G	зК	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 **ISSUE N**





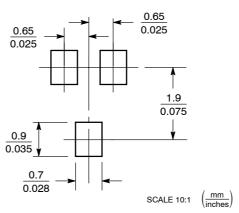
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3: PIN 1. BASE

2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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